

Application No.: 10/601,597

Docket No.: 2336-181

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1-4. (canceled)

5. (currently amended) A GaN light emitting diode, comprising:

a first conductive GaN clad layer which is a GaN crystalline layer doped with an n-type impurity;

~~with an upper surface provided with a first contact formed thereon on and in direct contact with an upper surface of the first conductive GaN clad layer;~~

an active layer formed on a lower surface of the first conductive GaN clad layer;

a second conductive GaN clad layer formed on a lower surface of the active layer, wherein the second conductive GaN clad layer is a GaN crystalline layer doped with a p-type impurity;

a conductive adhesive layer formed ~~[[on]]~~ below the second conductive GaN clad layer; ~~[[and]]~~

a conductive substrate, ~~with a lower surface provided with a second contact formed thereon,~~ formed on a lower surface of the conductive adhesive layer; and ~~[[,]]~~

a second contact formed on a lower surface of said conductive substrate;

wherein the conductive adhesive layer is made of a material selected from the group consisting of Au-Sn, Sn, In, Au-Ag and Pb-Sn.

6-23. (canceled)

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24. (new) The GaN light emitting diode as set forth in claim 5, further comprising a reflective layer made of a conductive material and formed between the second conductive GaN clad layer and the conductive adhesive layer.

25. (new) The GaN light emitting diode as set forth in claim 24, wherein the reflective layer is made of a material selected from the group consisting of Au, Ni, Ag, Al and alloys thereof.

26. (new) The GaN light emitting diode as set forth in claim 5, wherein the conductive substrate is made of a material selected from the group consisting of silicon (Si), germanium (Ge) and GaAs.